Ordering number : ENA1010A

ECH8651R

N-Channel Power MOSFET
24V, 10A, 14mΩ, Dual ECH8

ON Semiconductor®
http://onsemi.com

Features

- Low ON-resistance
- 2.5V drive
- Common-drain type
- Protection diode in
- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

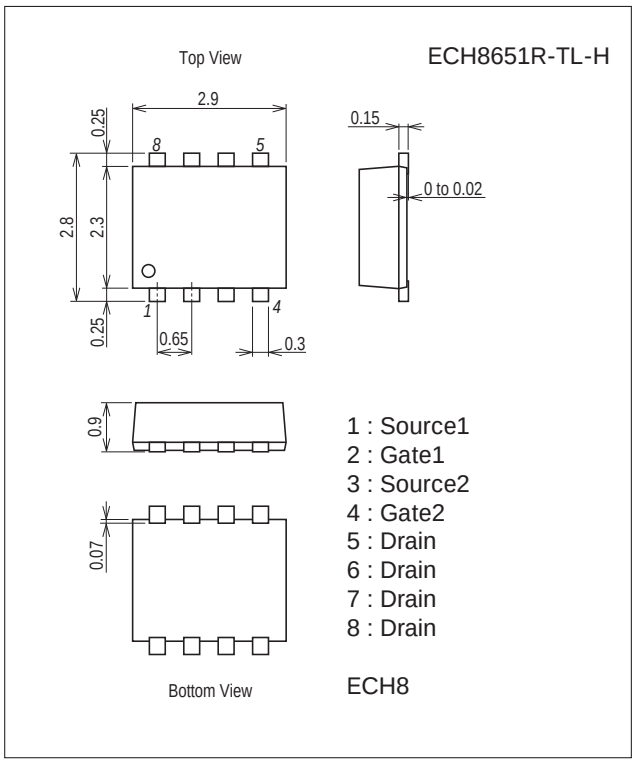
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		24	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		10	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm) 1unit	1.4	W
Total Dissipation	P_T	When mounted on ceramic substrate (900mm²×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

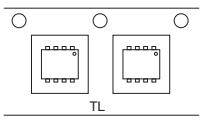
unit : mm (typ)
7011A-003



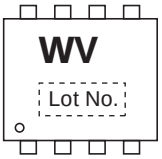
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

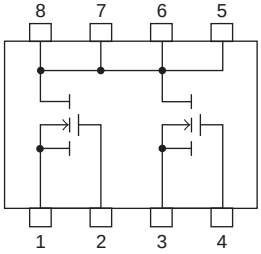
Packing Type : TL



Marking



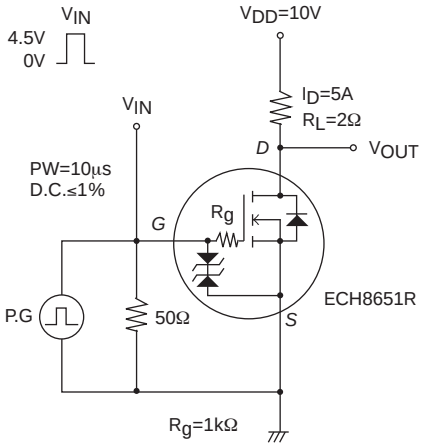
Electrical Connection



Electrical Characteristics at Ta=25°C

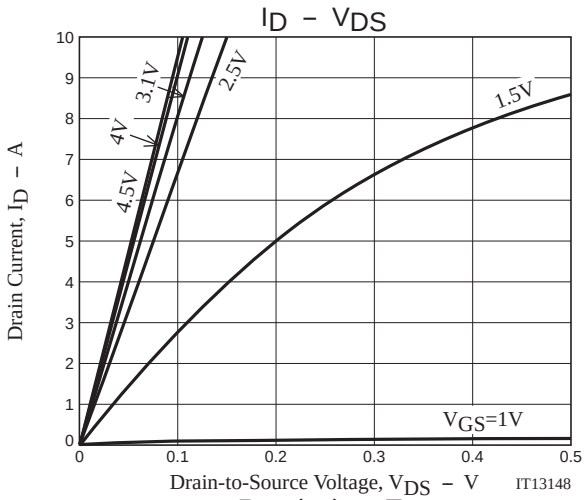
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	24			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.5		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=5A	5.5	9.5		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=5A, V_{GS}=4.5V	7	10.5	14	mΩ
	R_{DS}(on)2	I_D=5A, V_{GS}=4.0V	7.2	11	15	mΩ
	R_{DS}(on)3	I_D=5A, V_{GS}=3.1V	7.5	12.5	17.5	mΩ
	R_{DS}(on)4	I_D=2.5A, V_{GS}=2.5V	9	15	21	mΩ
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		300		ns
Rise Time	t_r			1000		ns
Turn-OFF Delay Time	$t_{d(off)}$			4000		ns
Fall Time	t_f			2500		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=10A		24		nC
Gate-to-Source Charge	Qgs			2		nC
Gate-to-Drain “Miller” Charge	Qgd			4.5		nC
Diode Forward Voltage	V_{SD}	I_S=10A, V_{GS}=0V		0.77	1.2	V

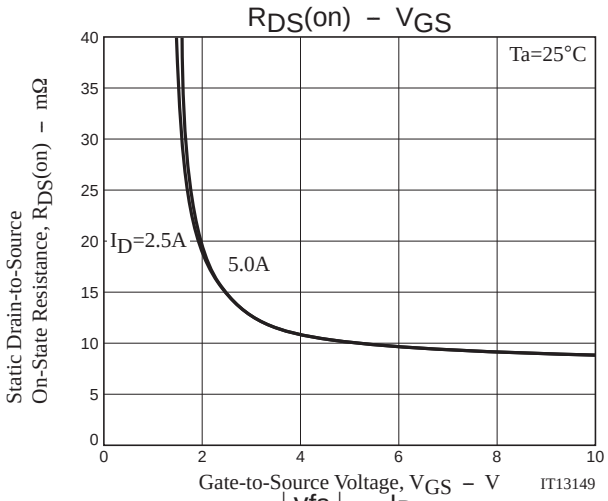
Switching Time Test Circuit

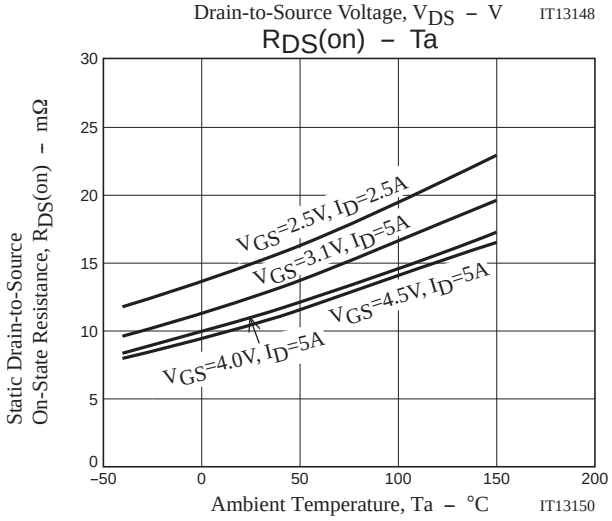


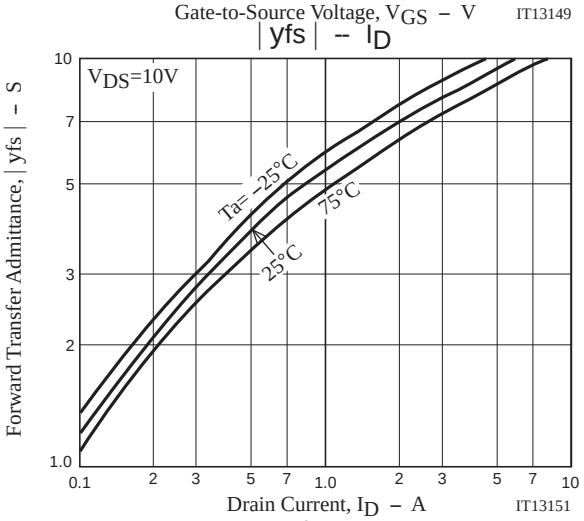
Ordering Information

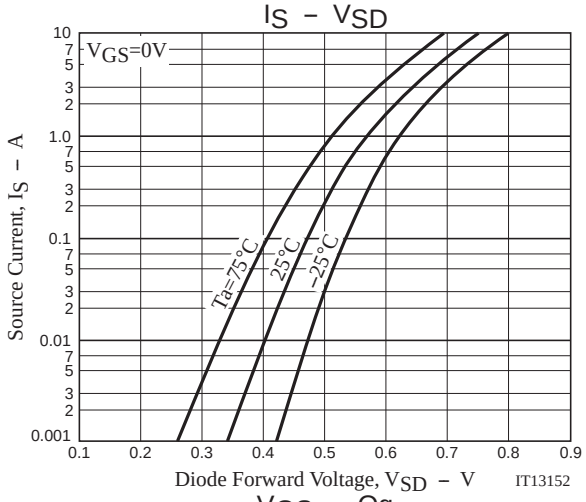
Device	Package	Shipping	memo
ECH8651R-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

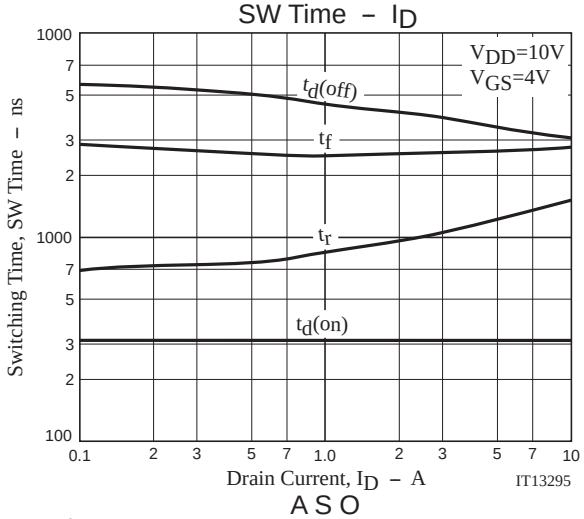


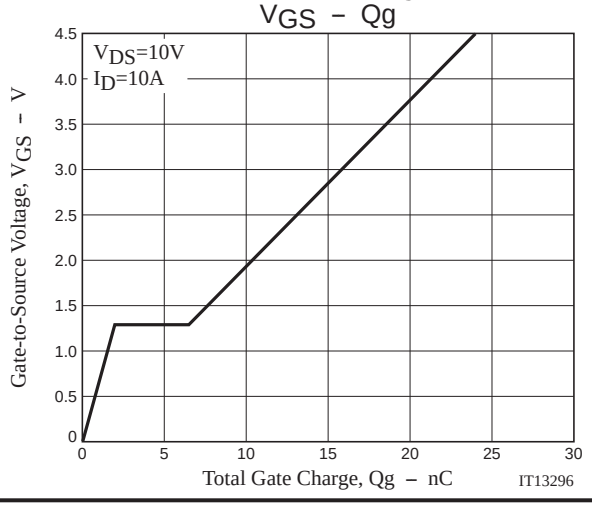


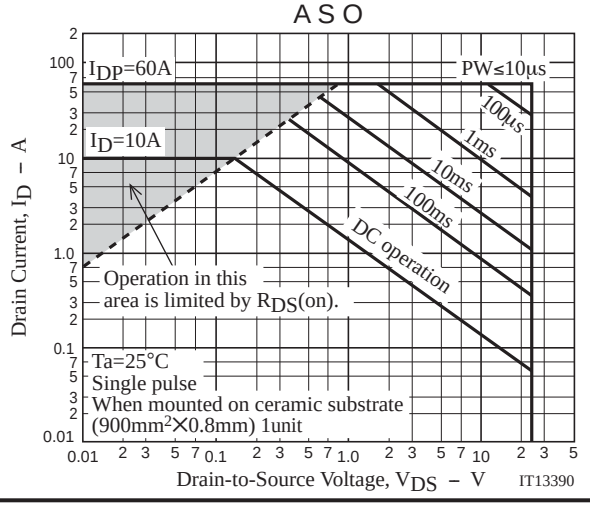


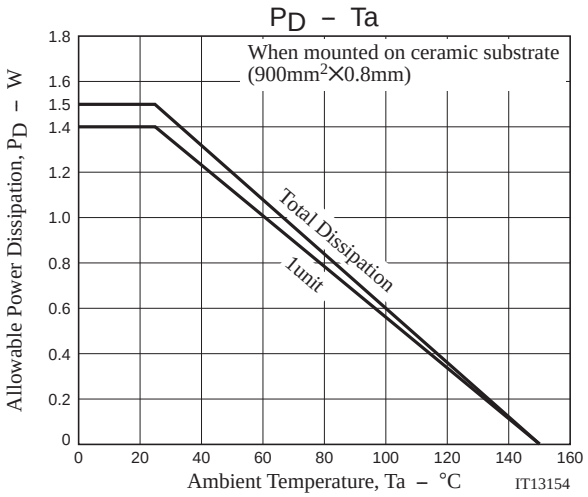












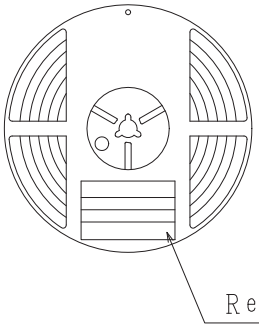
Embossed Taping Specification

ECH8651R-TL-H

1. Packing Format

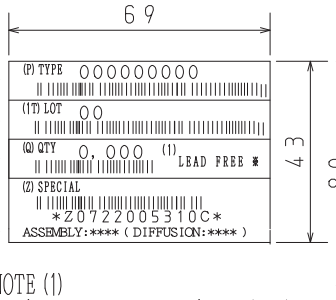
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



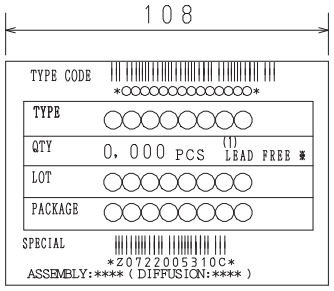
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



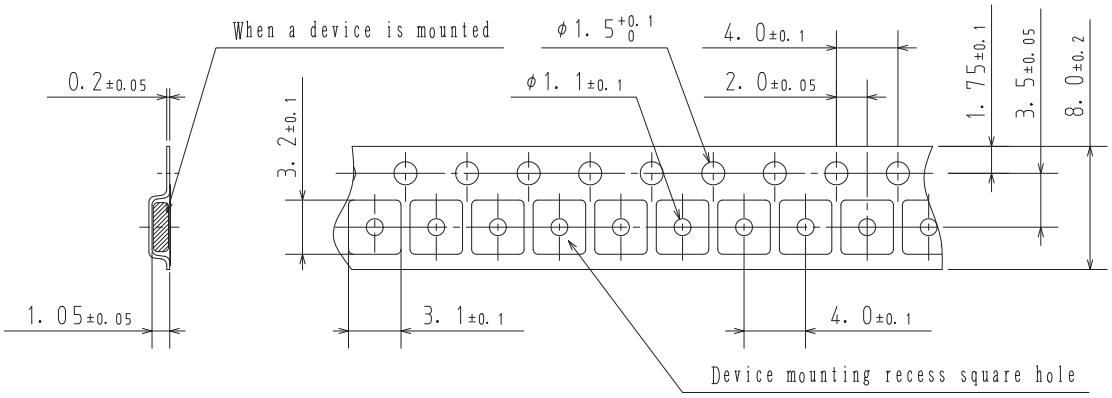
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

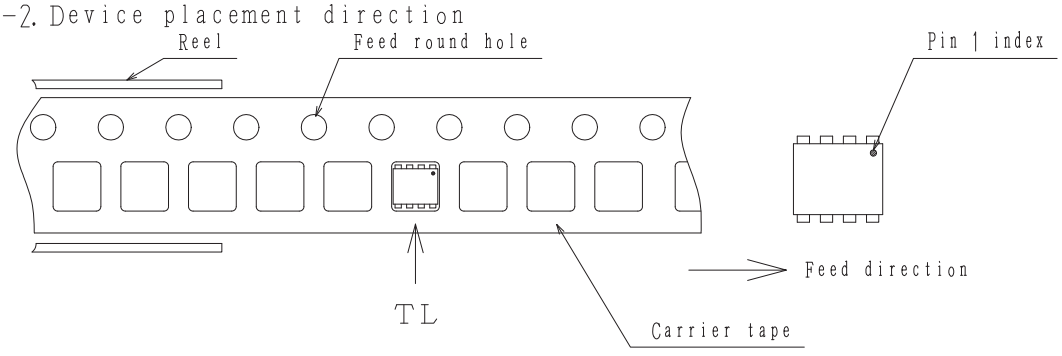
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



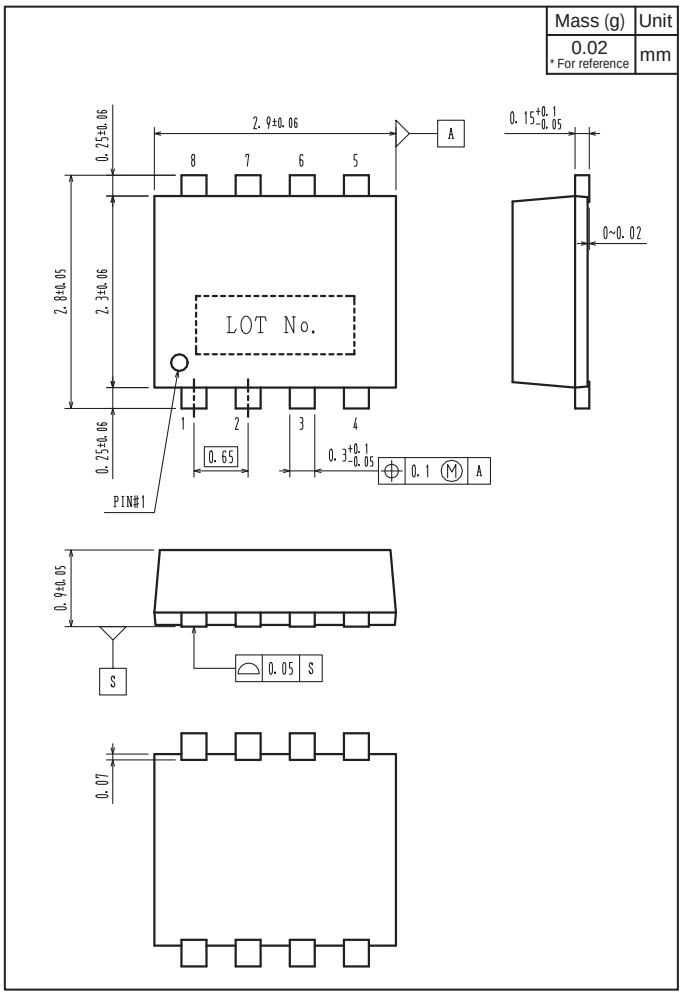
2-2. Device placement direction



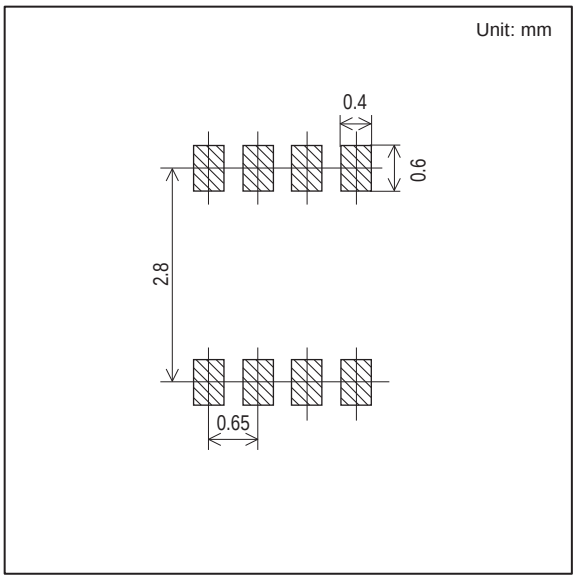
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

ECH8651R-TL-H



Land Pattern Example



Note on usage : Since the ECH8651R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.